Hex Schmitt-Trigger Inverter

High-Performance Silicon-Gate CMOS

The MC74HC14A is identical in pinout to the LS14, LS04 and the HC04. The device inputs are compatible with Standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC14A is useful to "square up" slow input rise and fall times. Due to hysteresis voltage of the Schmitt trigger, the HC14A finds applications in noisy environments.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7.0 A Requirements
- Chip Complexity: 60 FETs or 15 Equivalent Gates
- Pb-Free Packages are Available*



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MARKING DIAGRAMS



PDIP-14 N SUFFIX CASE 646





SOIC-14 D SUFFIX CASE 751A

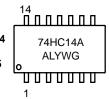




TSSOP-14 DT SUFFIX CASE 948G







A = Assembly Location

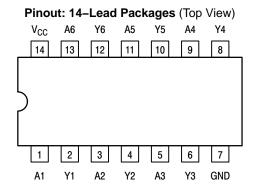
L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G = Pb−Free Package ■ Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

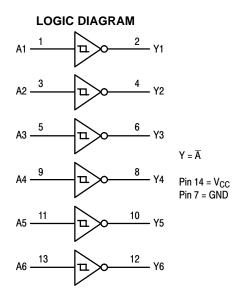
See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



FUNCTION TABLE

Inputs	Outputs
Α	Y
L	Н
Н	L



ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC14AN	PDIP-14	2000 Units / Box
MC74HC14ANG	PDIP-14 (Pb-Free)	2000 Units / Box
MC74HC14AD	SOIC-14	55 Units / Rail
MC74HC14ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HC14ADR2	SOIC-14	2500 Units / Reel
MC74HC14ADR2G	SOIC-14 (Pb-Free)	2500 Units / Reel
MC74HC14ADT	TSSOP-14*	96 Units / Rail
MC74HC14ADTG	TSSOP-14*	96 Units / Rail
MC74HC14ADTR2	TSSOP-14*	2500 Units / Reel
MC74HC14ADTR2G	TSSOP-14*	2500 Units / Reel
MC74HC14AF	SOEIAJ-14	50 Units / Rail
MC74HC14AFG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74HC14AFEL	SOEIAJ-14	2000 Units / Reel
MC74HC14AFELG	SOEIAJ-14 (Pb-Free)	2000 Units / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb–Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature Range, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise/Fall Time $V_{CC} = 2.0 \text{ V}$ (Figure 1) $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	No Limit* No Limit* No Limit*	ns

^{*}When $V_{in} = 50\% V_{CC}$, $I_{CC} > 1mA$

DC CHARACTERISTICS (Voltages Referenced to GND)

				v _{cc}	Guara	nteed Lin	nit	
Symbol	Parameter	Conditi	ion	V CC	−55 to 25°C	≤ 85 °C	≤125°C	Unit
V _{T+} max	Maximum Positive–Going Input Threshold Voltage (Figure 3)	$\begin{aligned} V_{out} &= 0.1V \\ I_{out} &\leq 20 \mu A \end{aligned}$		2.0 3.0 4.5 6.0	1.50 2.15 3.15 4.20	1.50 2.15 3.15 4.20	1.50 2.15 3.15 4.20	V
V _{T+} min	Minimum Positive–Going Input Threshold Voltage (Figure 3)	$\begin{aligned} V_{out} &= 0.1V \\ I_{out} &\leq 20 \mu A \end{aligned}$		2.0 3.0 4.5 6.0	1.0 1.5 2.3 3.0	0.95 1.45 2.25 2.95	0.95 1.45 2.25 2.95	V
V _T max	Maximum Negative–Going Input Threshold Voltage (Figure 3)	$\begin{aligned} V_{out} &= V_{CC} - 0.1V \\ I_{out} &\leq 20 \mu A \end{aligned}$		2.0 3.0 4.5 6.0	0.9 1.4 2.0 2.6	0.95 1.45 2.05 2.65	0.95 1.45 2.05 2.65	V
V _T min	Minimum Negative-Going Input Threshold Voltage (Figure 3)	$\begin{aligned} V_{out} &= V_{CC} - 0.1V \\ I_{out} &\leq 20 \mu A \end{aligned}$		2.0 3.0 4.5 6.0	0.3 0.5 0.9 1.2	0.3 0.5 0.9 1.2	0.3 0.5 0.9 1.2	V
V _H max Note 2	Maximum Hysteresis Voltage (Figure 3)	$V_{out} = 0.1V \text{ or } V_{CC}$ $ I_{out} \le 20\mu\text{A}$	- 0.1V	2.0 3.0 4.5 6.0	1.20 1.65 2.25 3.00	1.20 1.65 2.25 3.00	1.20 1.65 2.25 3.00	V
V _H min Note 2	Minimum Hysteresis Voltage (Figure 3)	$V_{out} = 0.1V \text{ or } V_{CC}$ $ I_{out} \le 20\mu\text{A}$	- 0.1V	2.0 3.0 4.5 6.0	0.20 0.25 0.40 0.50	0.20 0.25 0.40 0.50	0.20 0.25 0.40 0.50	٧
V _{OH}	Minimum High-Level Output Voltage	$V_{in} \le V_{T-} min$ $ I_{out} \le 20\mu A$		2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{in} \le V_{T-} min$	$\begin{aligned} I_{out} &\leq 2.4 \text{mA} \\ I_{out} &\leq 4.0 \text{mA} \\ I_{out} &\leq 5.2 \text{mA} \end{aligned}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} \ge V_{T+} \text{ max}$ $ I_{out} \le 20 \mu A$		2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in} \ge V_{T+}$ max	$\begin{aligned} I_{out} &\leq 2.4 \text{mA} \\ I_{out} &\leq 4.0 \text{mA} \\ I_{out} &\leq 5.2 \text{mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND		6.0	±0.1	±1.0	±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0\mu A$		6.0	1.0	10	40	μΑ

Information on typical parametric values along with frequency or heavy load considerations can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).
 V_Hmin > (V_{T+} min) - (V_{T-} max); V_Hmax = (V_{T+} max) - (V_{T-} min).

AC CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

			Guaranteed Limit			
Symbol	Parameter	V _{CC}	-55 to 25°C	≤85°C	≤125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 30 15 13	95 40 19 16	110 55 22 19	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance	•	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Inverter)*	22	pF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

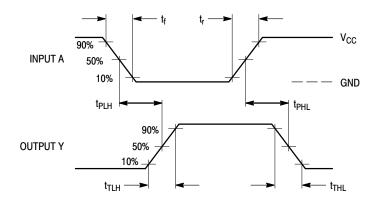
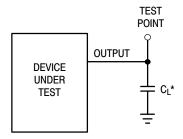


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance

Figure 2. Test Circuit

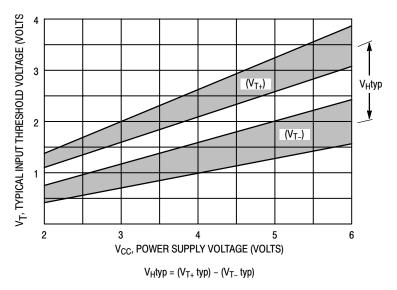
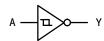
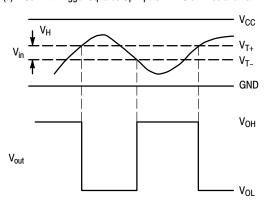


Figure 3. Typical Input Threshold, V_{T+} , V_{T-} versus Power Supply Voltage



(a) A Schmitt-Trigger Squares Up Inputs With Slow Rise and Fall Times



(b) A Schmitt-Trigger Offers Maximum Noise Immunity

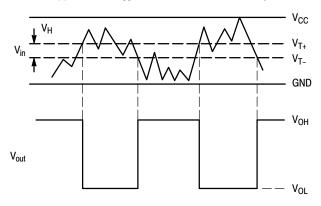
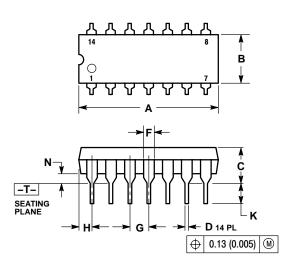
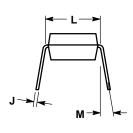


Figure 4. Typical Schmitt-Trigger Applications

PACKAGE DIMENSIONS

PDIP-14 **N SUFFIX** CASE 646-06 **ISSUE N**





NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING
 PER ANSI Y14.5M, 1982.

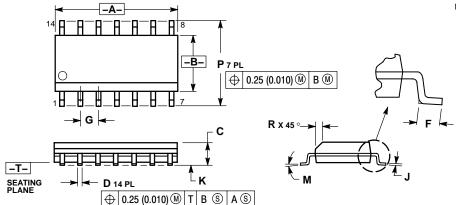
 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION L TO CENTER OF LEADS
 WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	18.80
В	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
Н	0.052	0.095	1.32	2.41
7	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M		10 °		10 °
N	0.015	0.039	0.38	1.01

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE G**



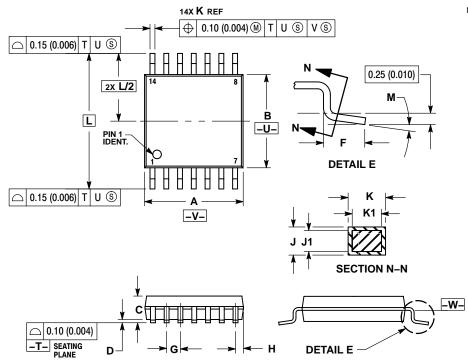
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- 4. MAAIMUM MOLD PROTRUSION 0.15 (0.0)
 PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.127
 (0.005) TOTAL IN EXCESS OF THE D
 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE A**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 - DIMENSION AT MAXIMUM MATERIAL CONDITION.

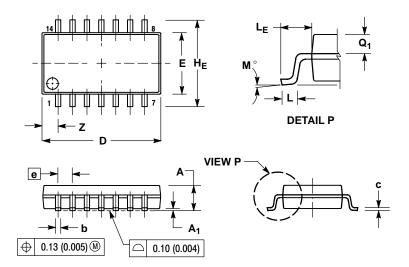
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252	BSC
M	0°	8 °	0 °	8 °

PACKAGE DIMENSIONS

SOEIAJ-14 **F SUFFIX** CASE 965-01 **ISSUE O**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		1.42		0.056

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